

P-Channel MOSFET

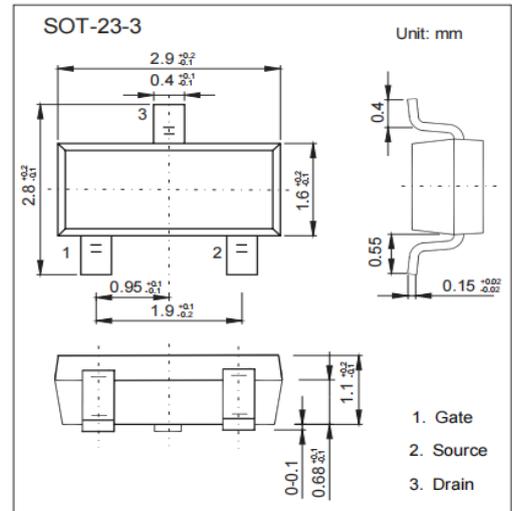
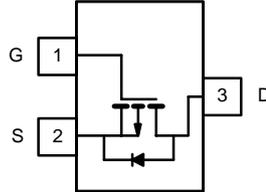
RC6P04

■ Features

- $V_{DS} (V) = -40V$
- $I_D = -6.0A$
- $R_{DS(ON)} < 40m\Omega (V_{GS} = -10V)$
- $R_{DS(ON)} < 60m\Omega (V_{GS} = -4.5V)$

Marking

Marking	230S
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■ Maximum ratings ($T_a = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current	-6	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current	-4.6	A
I_{DM}	Pulsed Drain Current ²	-25	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ³	2.0	W
$P_D @ T_A = 70^\circ C$	Total Power Dissipation ³	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	65	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10s$)	---	55	$^\circ C/W$

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■ Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-40	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.014	---	V/°C
R _{DS(on)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-3A	---	34	40	mΩ
		V _{GS} =-4.5V, I _D =-3A	---	45	60	
		V _{GS} =-2.5V, I _D =-2A	---	---	---	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	---	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	2.6	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-24V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-3A	---	5.6	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-3A	---	11.9	---	nC
Q _{gs}	Gate-Source Charge		---	1.8	---	
Q _{gd}	Gate-Drain Charge		---	3	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-15V, V _{GS} =-4.5V, R _G =3.3Ω, I _D =-3A	---	6.6	---	ns
T _r	Rise Time		---	27.8	---	
T _{d(off)}	Turn-Off Delay Time		---	46.2	---	
T _f	Fall Time		---	20.6	---	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	920	---	pF
C _{oss}	Output Capacitance		---	73	---	
C _{rss}	Reverse Transfer Capacitance		---	71	---	

■ Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _s	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-6.0	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _s =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

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■ Typical Characteristics

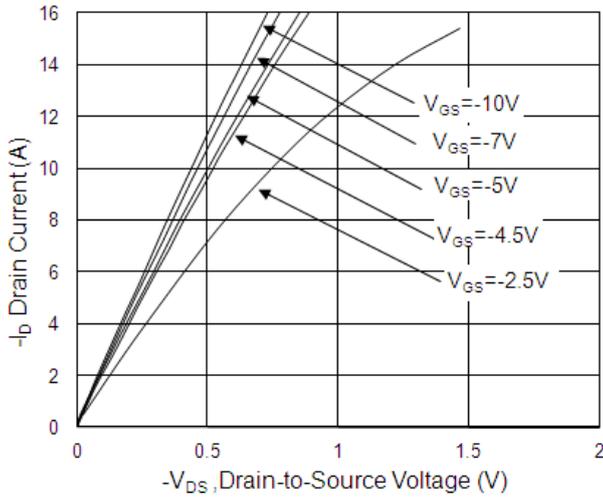


Fig.1 Typical Output Characteristics

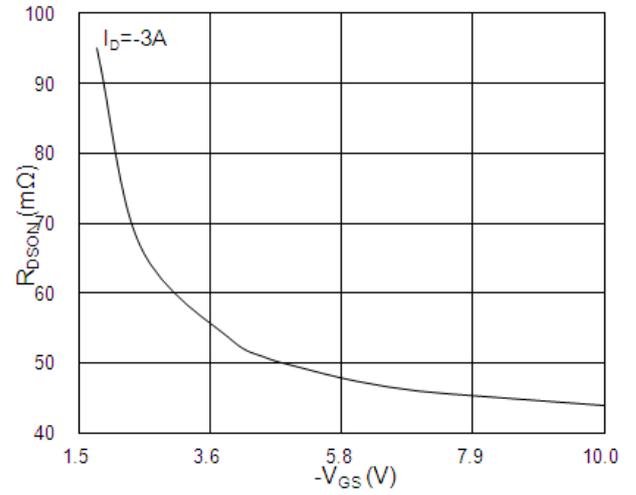


Fig.2 On-Resistance vs. G-S Voltage

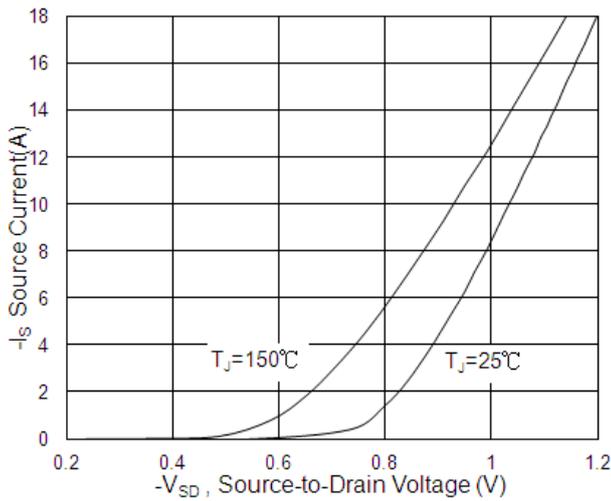


Fig.3 Forward Characteristics Of Reverse

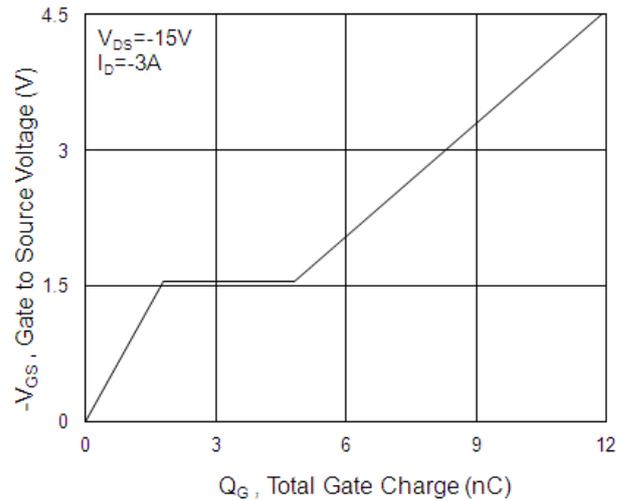


Fig.4 Gate-Charge Characteristics

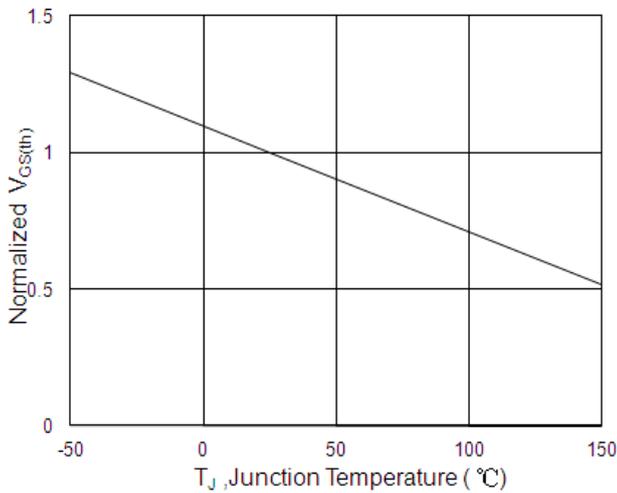


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

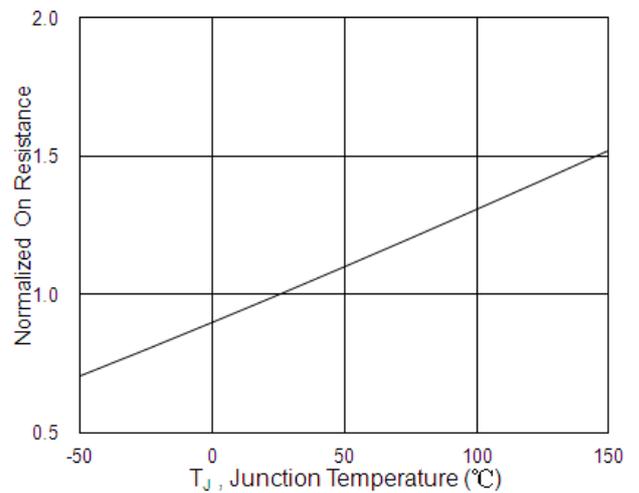


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

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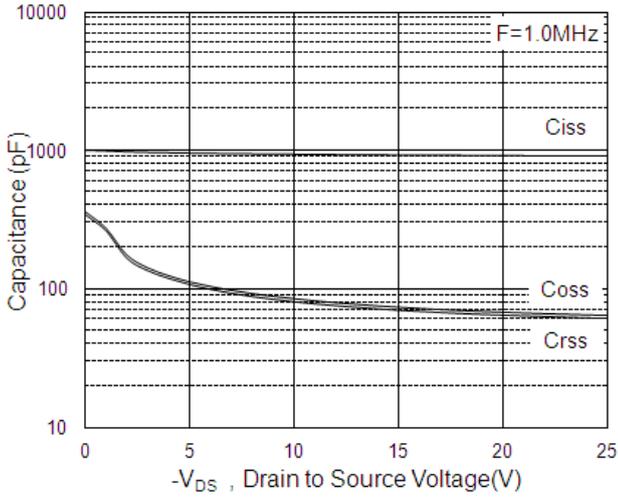


Fig.7 Capacitance

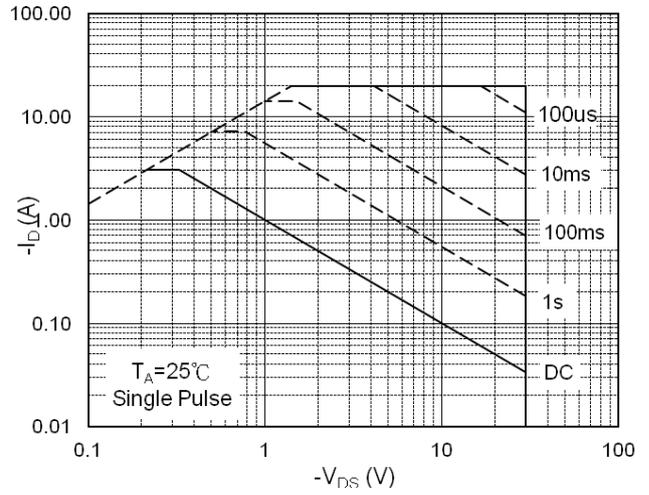


Fig.8 Safe Operating Area

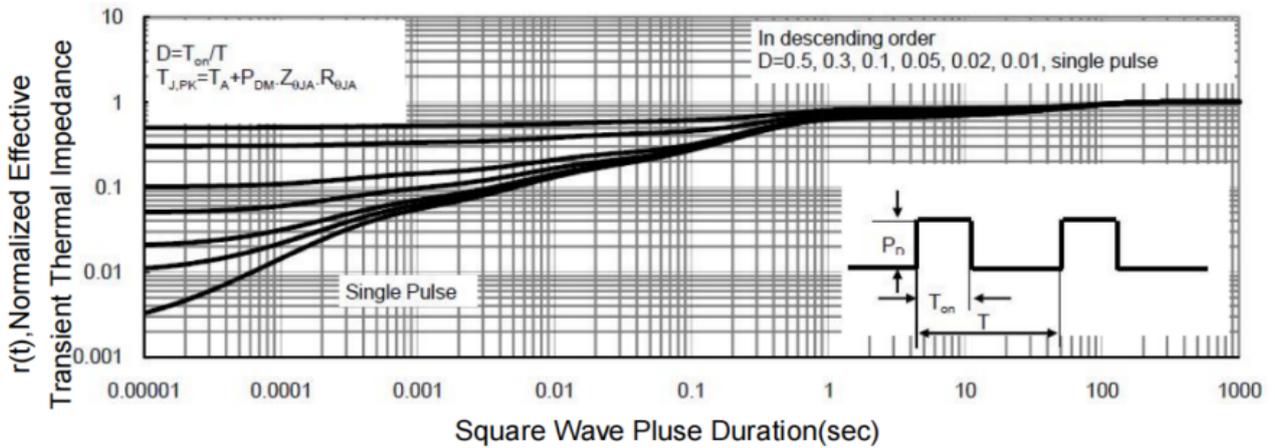


Fig.9 Normalized Maximum Transient Thermal Impedance

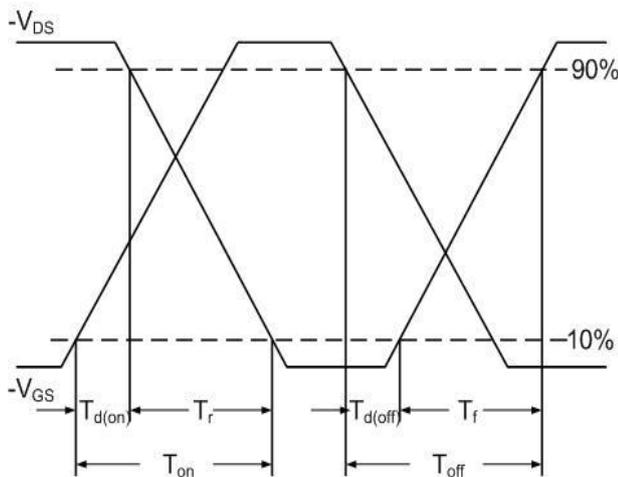


Fig.10 Switching Time Waveform

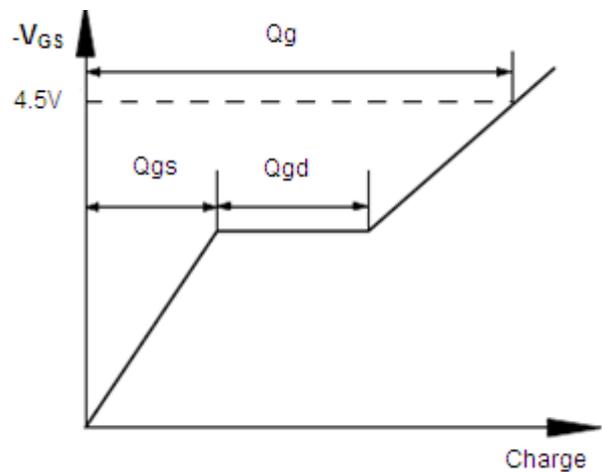


Fig.11 Gate Charge Waveform